

ABSTRACT

A low temperature sintering ceramic composition that can be sintered at a temperature equal to or less than 1000 °C and has low dielectric constant and dielectric loss in a high frequency region of 17 Ghz or more, an electronic component using the same and a method of fabricating the low temperature sintering ceramic are provided. The composition comprises MgO and SiO<sub>2</sub> in sum total in the range of from 64.0 to 99.2% by mass; Bi<sub>2</sub>O<sub>3</sub> in the range of from 0.4 to 33.0% by mass; Li<sub>2</sub>O in the range of from 0.4 to 3.0% by mass; and MgO and SiO<sub>2</sub> are contained in the molar ratio of from 2: 1 to 2: 3.5, at least part thereof being contained as a complex oxide of Mg and Si.